

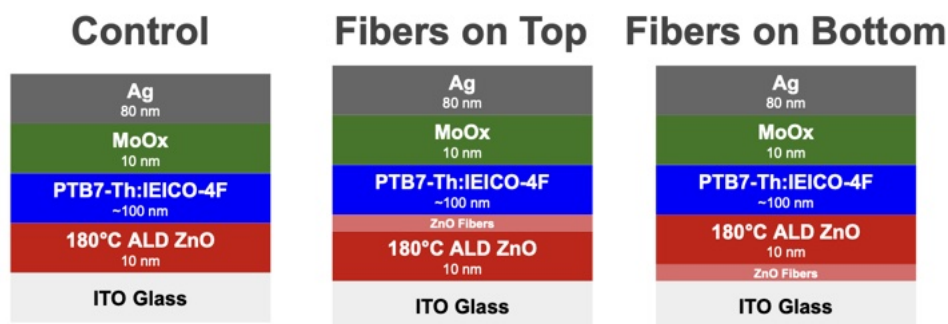


Figure 1: Device schematics. Each ZnO condition was annealed at 400°C for 2 hours in air.

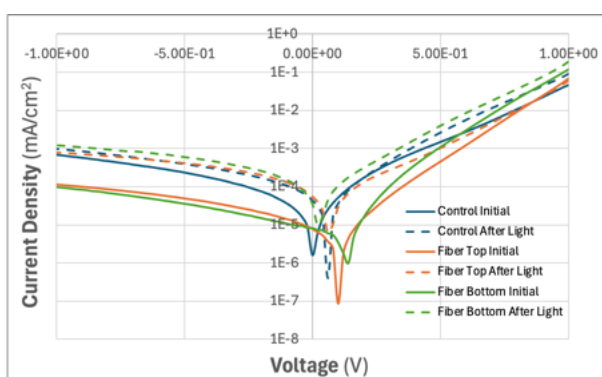


Figure 2: J_{Dark} -V plots for devices before light exposure and after light exposure (1.5 AMG, 5 minutes).

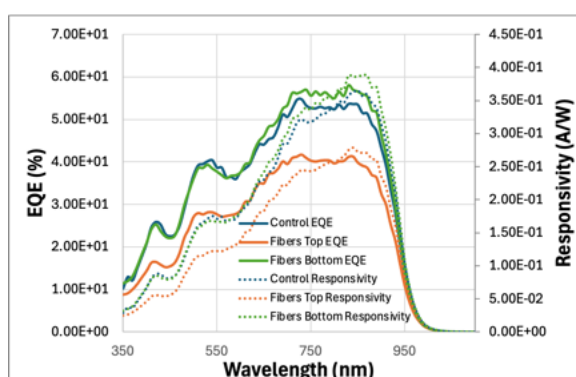


Figure 3: EQE and responsivity for devices. Fibers on Bottom devices showed enhanced EQE and responsivity.

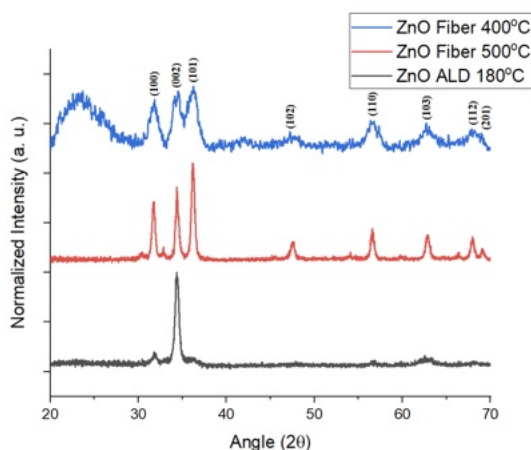


Figure 4: GIXRD for ZnO nanofibers calcined at 400°C and 500°C and ALD ZnO deposited at 180°C.

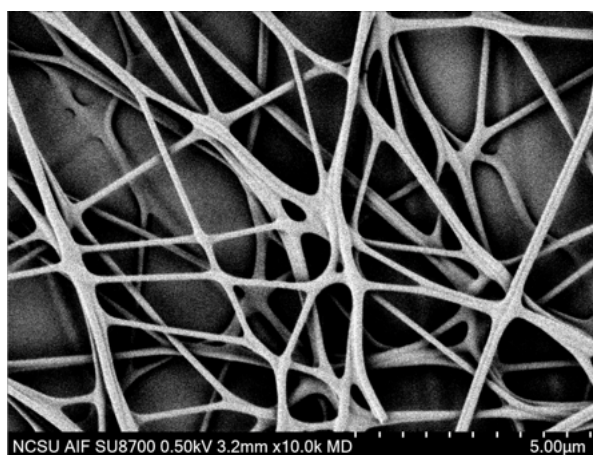


Figure 5: SEM micrograph of ZnO nanofibers after calcining at 400°C for 2 hours.